Abstract

Integrated field-effect transistor with two control regions, use of this field-effect transistor and fabrication method

An explanation is given of, inter alia, a field-effect transistor (10) fabricated as a so-called double gate transistor (10) using the SOI technique and the salicide technique. The transistor (10) is suitable for switching voltages of greater than five volts or even greater than nine volts and requires only a very small chip area.

(Figure 1)



162162



G00002